



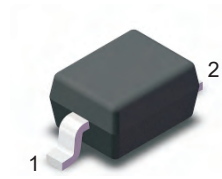
1SS355WB

Silicon Epitaxial Planar Switching Diode

Features

- For surface mount applications
- High Speed : $t_f=1.2\text{ns}$ Typ.
- High speed switching
- High reliability with high surge current handling capability

SOD-323W



1.Cathode —|<— 2.Anode

Marking Code: A

Absolute Maximum Ratings at $T_A = 25\text{ }^\circ\text{C}$

Parameter	Symbol	1SS355WB	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	90	V
DC Reverse Voltage	V_R	80	V
Peak Forward Current	I_{FM}	225	mA
Average Rectified Output Current	I_O	100	mA
Surge Current (1s)	I_{surge}	500	mA
Operating Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 to +125	$^\circ\text{C}$

Characteristics at $T_A = 25\text{ }^\circ\text{C}$

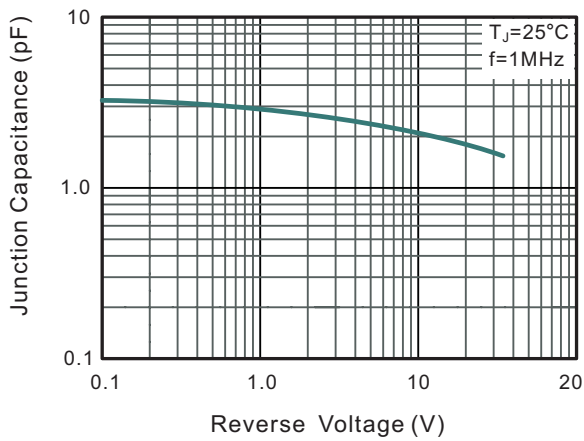
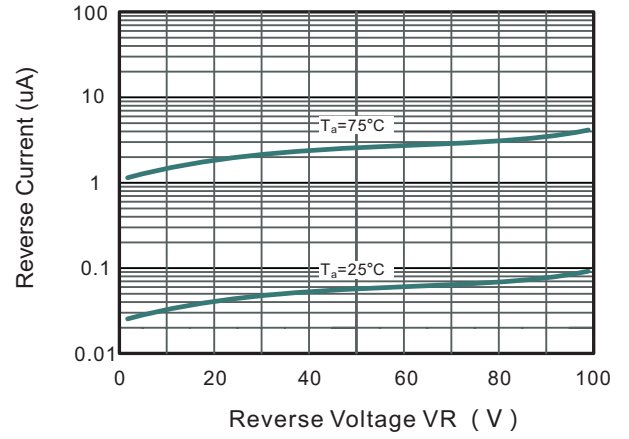
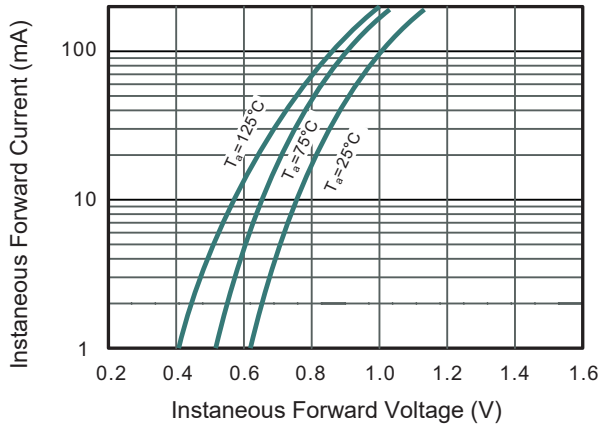
Parameter	Symbol	1SS355WB	Unit
Forward Voltage $I_F = 100\text{ mA}$	V_F	1.2	V
Reverse Current $V_R = 80\text{ V}$	I_R	0.1	μA
Capacitance Between Terminals at $V_R = 0.5\text{ V}$, $f = 1\text{ MHz}$	C_T	3	pF
Reverse Recovery Time at $V_R = 6\text{ V}$, $I_F = 10\text{ mA}$, $R_L = 100\text{ }\Omega$	T_{rr}	4	nS



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Typical Characteristic Curves





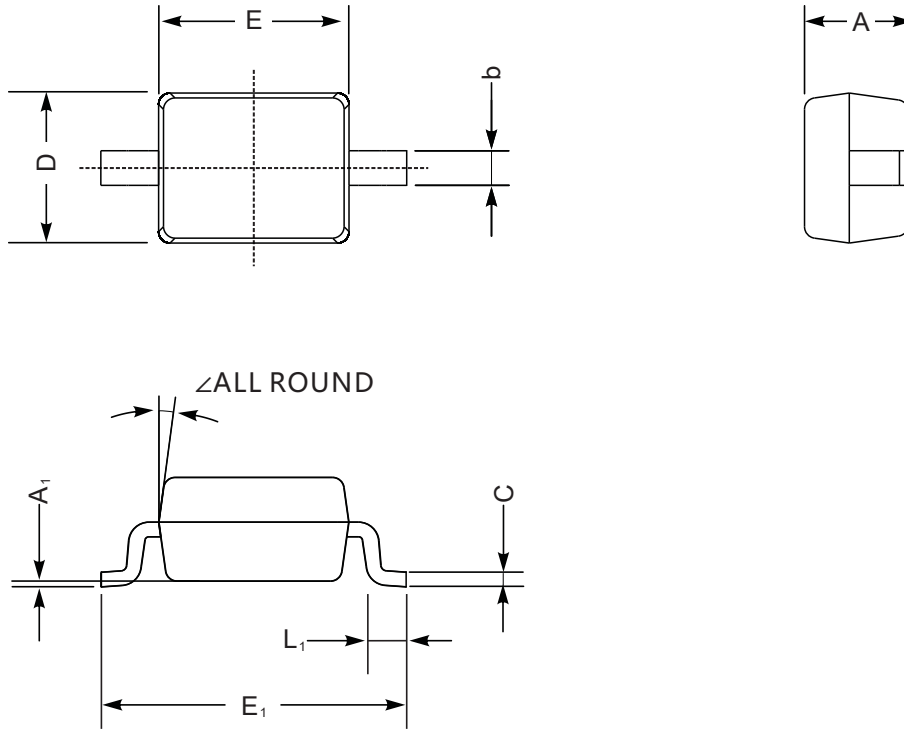
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Package Outline

SOD-323W

Dimensions in mm



UNIT		A	C	D	E	E ₁	b	L ₁	A ₁	∠
mm	max	1.1	0.15	1.4	1.8	2.75	0.4	0.45	0.2	9°
	min	0.8	0.08	1.2	1.4	2.55	0.25	0.2	—	
mil	max	43	5.9	55	70	108	16	16	8	
	min	32	3.1	47	63	100	9.8	7.9	—	